

PMV65UN

20 V, single N-channel Trench MOSFET

13 November 2012

Product data sheet

1. Product profile

1.1 General description

N-channel enhancement mode Field-Effect Transistor (FET) in a small SOT23 (TO-236AB) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

1.2 Features and benefits

- Low threshold voltage
- Very fast switching
- Trench MOSFET technology

1.3 Applications

- Relay driver
- High-speed line driver
- Low-side loadswitch
- Switching circuits

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{DS}	drain-source voltage	$T_{amb} = 25\text{ °C}$	-	-	20	V
V_{GS}	gate-source voltage		-8	-	8	V
I_D	drain current	$V_{GS} = 4.5\text{ V}; T_{amb} = 25\text{ °C}; t \leq 5\text{ s}$	[1]	-	2.2	A
Static characteristics						
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = 4.5\text{ V}; I_D = 2\text{ A}; T_j = 25\text{ °C}$	-	64	76	mΩ

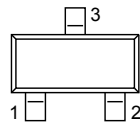
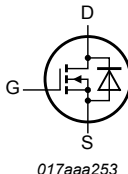
[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm².

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2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	 <p>TO-236AB (SOT23)</p>	 <p>017aaa253</p>
2	S	source		
3	D	drain		

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PMV65UN	TO-236AB	plastic surface-mounted package; 3 leads	SOT23

4. Marking

Table 4. Marking codes

Type number	Marking code
PMV65UN	ED%

[1] % = placeholder for manufacturing site code

5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{DS}	drain-source voltage	$T_{amb} = 25\text{ °C}$		-	20	V
V_{GS}	gate-source voltage			-8	8	V
I_D	drain current	$V_{GS} = 4.5\text{ V}; T_{amb} = 25\text{ °C}; t \leq 5\text{ s}$	[1]	-	2.2	A
		$V_{GS} = 4.5\text{ V}; T_{amb} = 25\text{ °C}$	[1]	-	2	A
		$V_{GS} = 4.5\text{ V}; T_{amb} = 100\text{ °C}$	[1]	-	1.3	A
I_{DM}	peak drain current	$T_{amb} = 25\text{ °C};$ single pulse; $t_p \leq 10\text{ }\mu\text{s}$		-	8	A
P_{tot}	total power dissipation	$T_{amb} = 25\text{ °C}$	[2]	-	310	mW
			[1]	-	455	mW
		$T_{sp} = 25\text{ °C}$		-	2170	mW

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Symbol	Parameter	Conditions		Min	Max	Unit
T_j	junction temperature			-55	150	°C
T_{amb}	ambient temperature			-55	150	°C
T_{stg}	storage temperature			-65	150	°C
Source-drain diode						
I_s	source current	$T_{amb} = 25\text{ °C}$	[1]	-	0.7	A

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm^2 .

[2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	350	402	K/W
			[2]	-	240	275	K/W
		in free air; $t \leq 5\text{ s}$	[2]	-	195	225	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point			-	50	58	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm^2 .

7. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
Static characteristics							
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 250\text{ }\mu\text{A}$; $V_{GS} = 0\text{ V}$; $T_j = 25\text{ °C}$		20	-	-	V
V_{GSth}	gate-source threshold voltage	$I_D = 250\text{ }\mu\text{A}$; $V_{DS} = V_{GS}$; $T_j = 25\text{ °C}$		0.4	0.7	1	V
I_{DSS}	drain leakage current	$V_{DS} = 20\text{ V}$; $V_{GS} = 0\text{ V}$; $T_{amb} = 25\text{ °C}$		-	-	1	μA
I_{GSS}	gate leakage current	$V_{GS} = 8\text{ V}$; $V_{DS} = 0\text{ V}$; $T_j = 25\text{ °C}$		-	-	100	nA

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Symbol	Parameter	Conditions	Min	Typ	Max	Unit
		$V_{GS} = -8\text{ V}; V_{DS} = 0\text{ V}; T_j = 25\text{ }^\circ\text{C}$	-	-	-100	nA
R_{DSon}	drain-source on-state resistance	$V_{GS} = 4.5\text{ V}; I_D = 2\text{ A}; T_j = 25\text{ }^\circ\text{C}$	-	64	76	m Ω
		$V_{GS} = 4.5\text{ V}; I_D = 2\text{ A}; T_j = 150\text{ }^\circ\text{C}$	-	94	111	m Ω
		$V_{GS} = 2.5\text{ V}; I_D = 1.7\text{ A}; T_j = 25\text{ }^\circ\text{C}$	-	78	97	m Ω
		$V_{GS} = 1.8\text{ V}; I_D = 0.8\text{ A}; T_j = 25\text{ }^\circ\text{C}$	-	110	156	m Ω
g_{fs}	forward transconductance	$V_{DS} = 10\text{ V}; I_D = 2\text{ A}; T_j = 25\text{ }^\circ\text{C}$	-	8.7	-	S
Dynamic characteristics						
$Q_{G(tot)}$	total gate charge	$V_{DS} = 10\text{ V}; I_D = 2\text{ A}; V_{GS} = 4.5\text{ V}; T_j = 25\text{ }^\circ\text{C}$	-	2.6	3.9	nC
Q_{GS}	gate-source charge		-	0.3	-	nC
Q_{GD}	gate-drain charge		-	0.7	-	nC
C_{iss}	input capacitance	$V_{DS} = 10\text{ V}; f = 1\text{ MHz}; V_{GS} = 0\text{ V}; T_j = 25\text{ }^\circ\text{C}$	-	183	-	pF
C_{oss}	output capacitance		-	52	-	pF
C_{rss}	reverse transfer capacitance		-	26	-	pF
$t_{d(on)}$	turn-on delay time	$V_{DS} = 10\text{ V}; I_D = 2\text{ A}; V_{GS} = 4.5\text{ V}; R_{G(ext)} = 6\text{ }^\circ\Omega; T_j = 25\text{ }^\circ\text{C}$	-	6	-	ns
t_r	rise time		-	18	-	ns
$t_{d(off)}$	turn-off delay time		-	21	-	ns
t_f	fall time		-	12	-	ns
Source-drain diode						
V_{SD}	source-drain voltage	$I_S = 0.7\text{ A}; V_{GS} = 0\text{ V}; T_j = 25\text{ }^\circ\text{C}$	-	0.8	1.2	V